

2SK2725

Silicon N Channel MOS FET
High Speed Power Switching

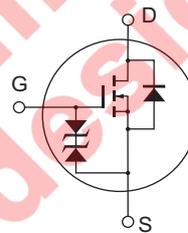
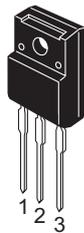
REJ03G1023-0400
(Previous: ADE-208-452B)
Rev.4.00
Sep 07, 2005

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Avalanche ratings

Outline

RENESAS Package code: PRSS0003AE-A
(Package name: TO-220C•FM)



1. Gate
2. Drain
3. Source

Not recommended
for new design

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	5	A
Drain peak current	$I_{D(pulse)}^{*1}$	20	A
Body to drain diode reverse drain current	I_{DR}	5	A
Avalanche current	I_{AP}^{*3}	5	A
Avalanche energy	E_{AR}^{*3}	1.38	mJ
Channel dissipation	P_{ch}^{*2}	30	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

- Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

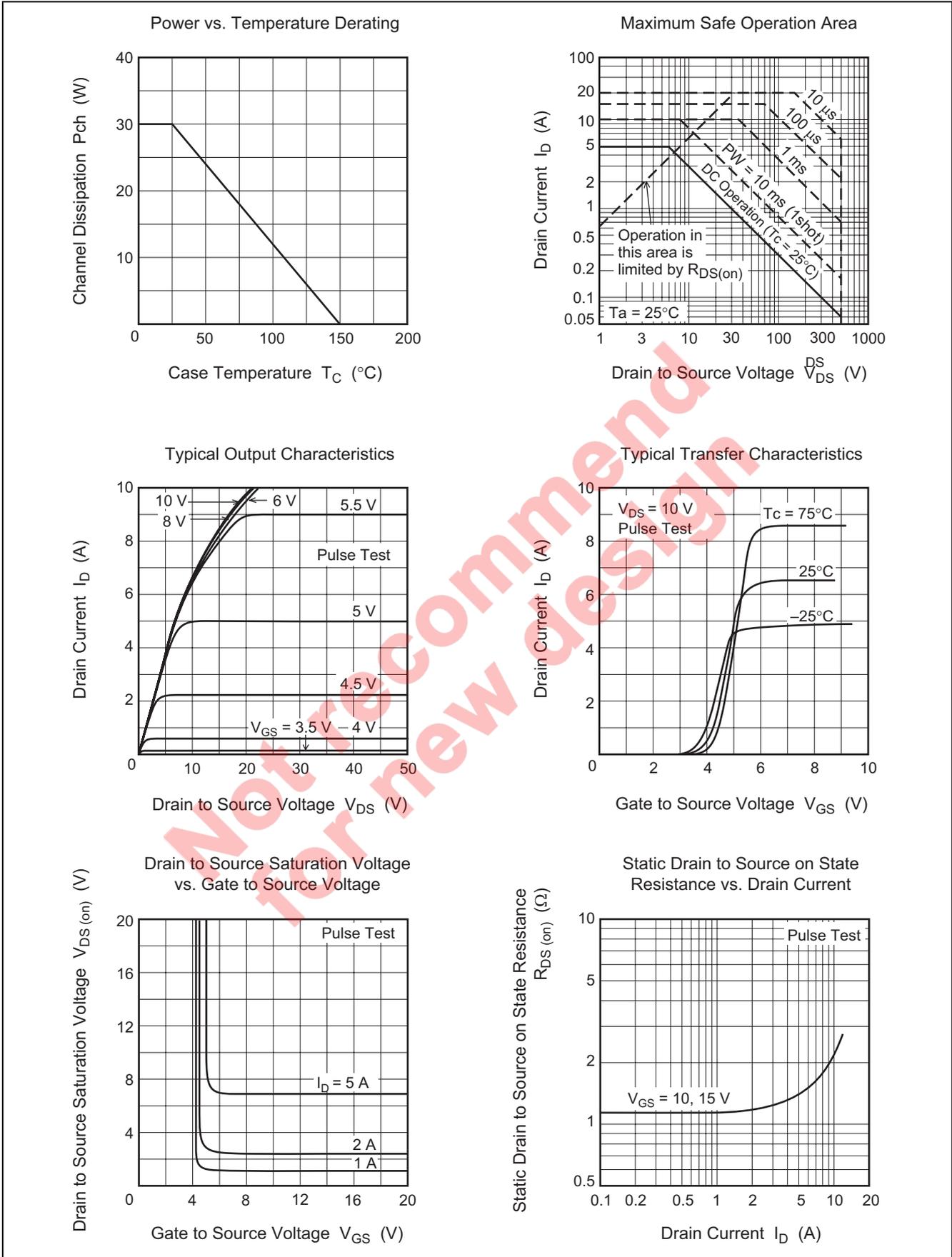
Electrical Characteristics

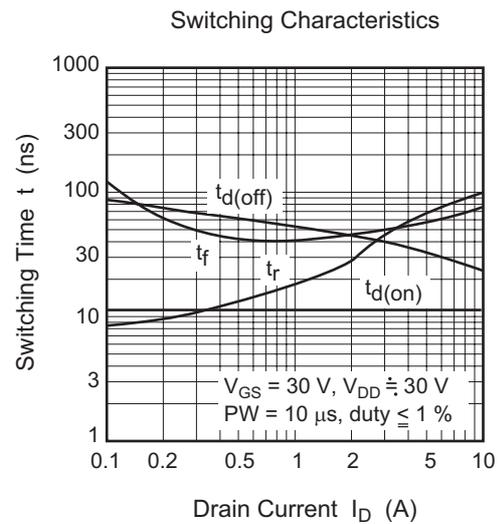
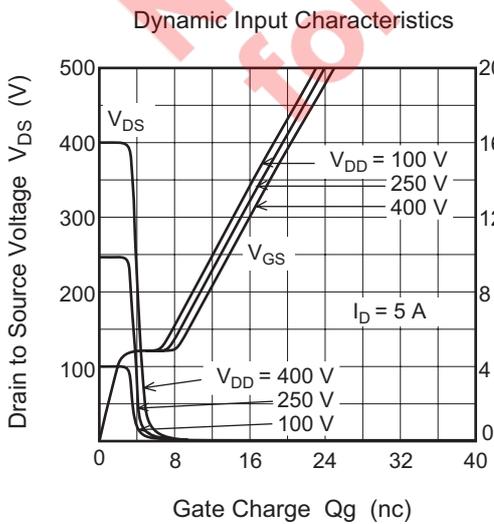
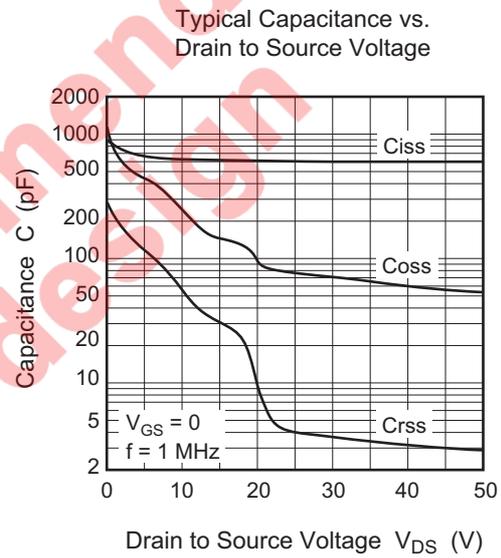
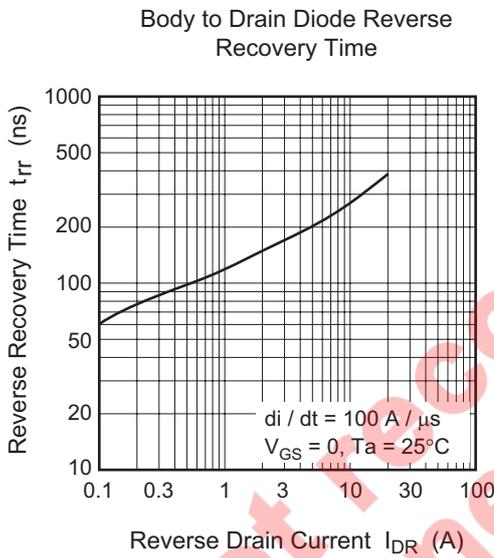
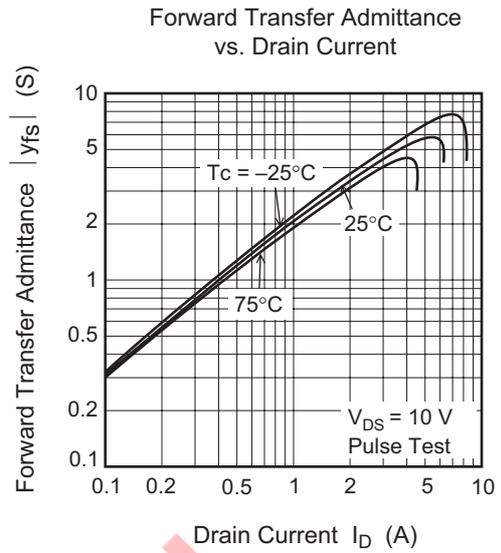
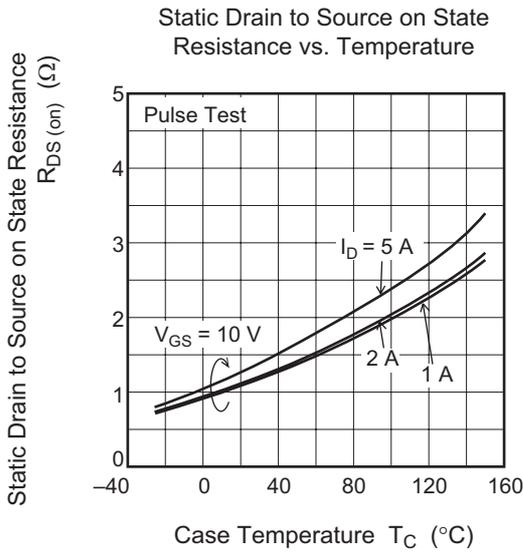
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 500 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.5	—	3.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}^{*4}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.2	1.6	Ω	$I_D = 3 \text{ A}$, $V_{GS} = 10 \text{ V}^{*4}$
Forward transfer admittance	$ y_{fs} $	2.5	4.5	—	S	$I_D = 3 \text{ A}$, $V_{DS} = 10 \text{ V}^{*4}$
Input capacitance	C_{iss}	—	630	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	250	—	pF	
Reverse transfer capacitance	C_{rss}	—	55	—	pF	
Total gate charge	Q_g	—	13.5	—	nc	$V_{DD} = 400 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 5 \text{ A}$
Gate to source charge	Q_{gs}	—	3.5	—	nc	
Gate to drain charge	Q_{gd}	—	5.0	—	nc	
Turn-on delay time	$t_{d(on)}$	—	11	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$, $R_L = 10 \Omega$
Rise time	t_r	—	45	—	ns	
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	50	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_D = 5 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = 5 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu s$

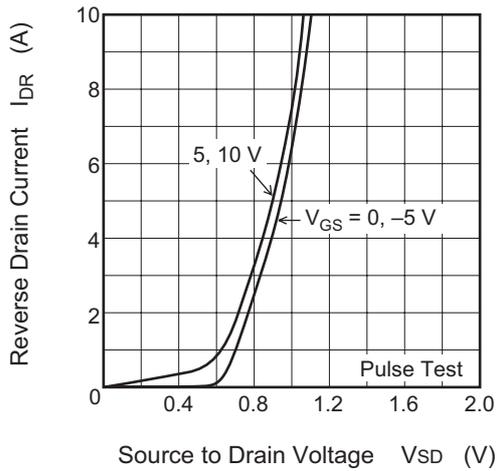
- Note: 4. Pulse test

Main Characteristics

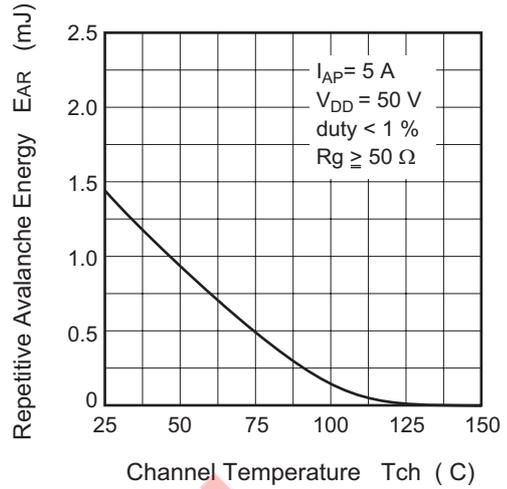




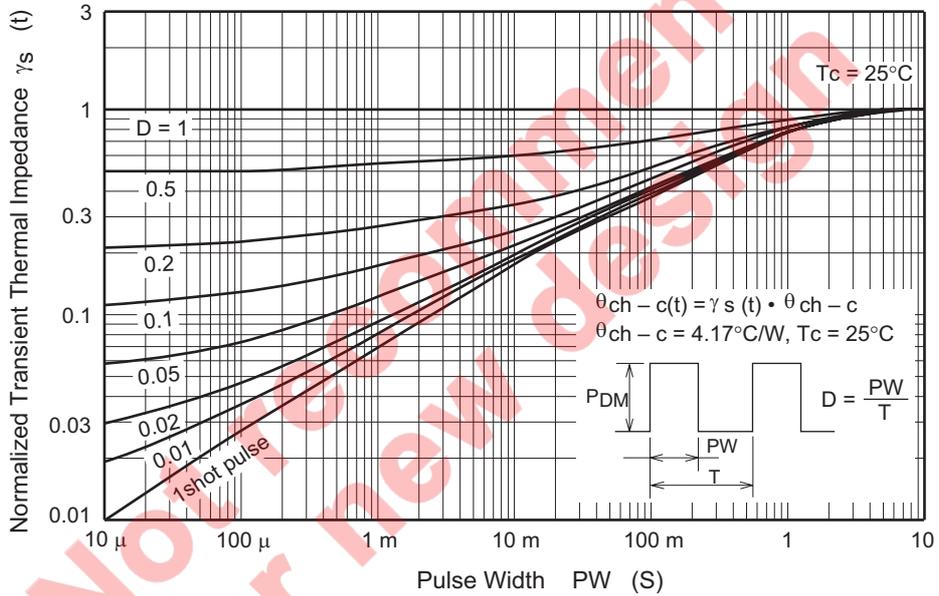
Reverse Drain Current vs. Source to Drain Voltage



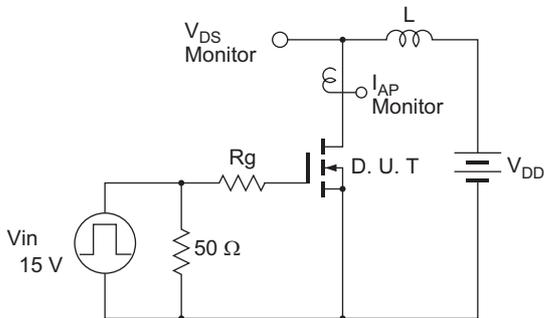
Maximum Avalanche Energy vs. Channel Temperature Derating



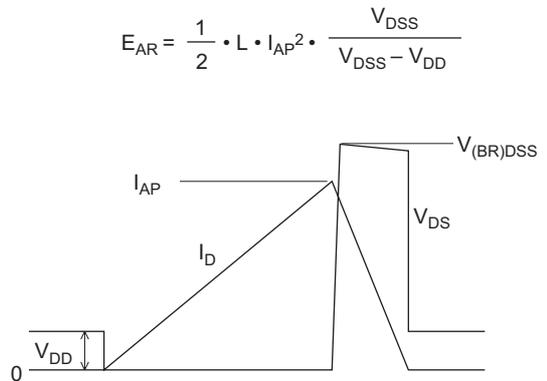
Normalized Transient Thermal Impedance vs. Pulse Width

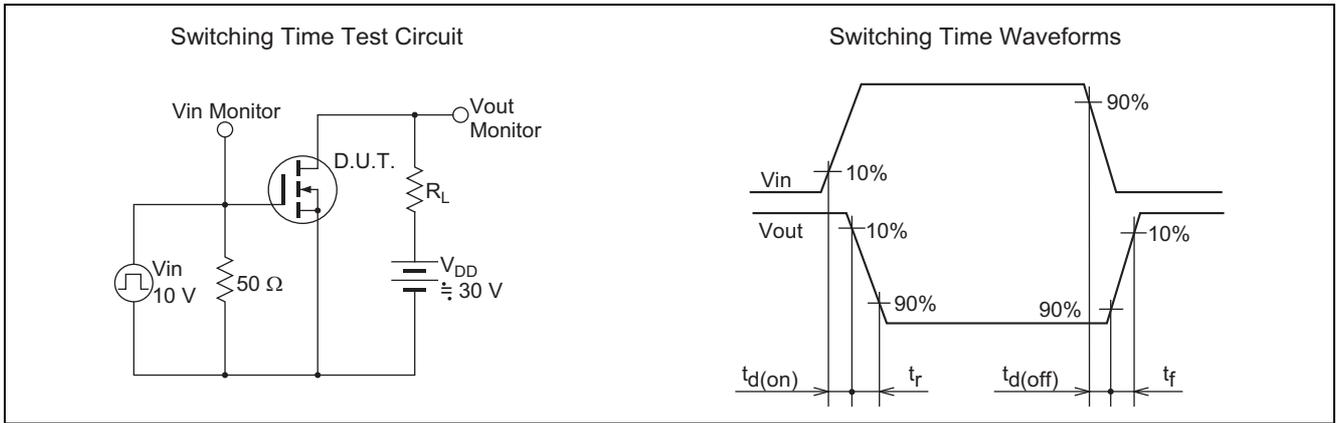


Avalanche Test Circuit



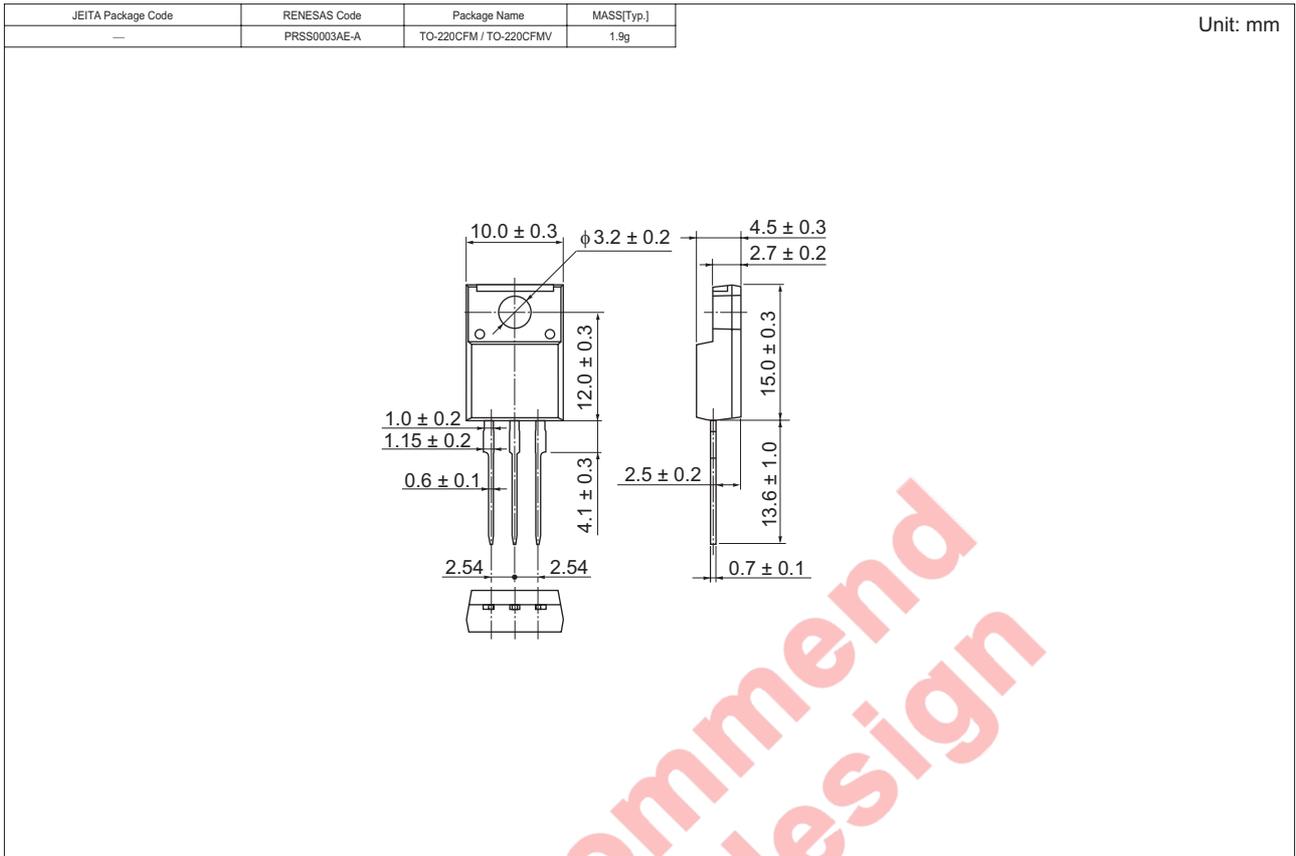
Avalanche Waveform





Not recommend
for new design

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2725-E	600 pcs	Box (Tube)

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